B11G3338N80D

LDMOS 3-stage integrated Doherty MMIC

AMPLEON

Rev. 2 — 7 April 2022

Product data sheet

1. Product profile

1.1 General description

The B11G3338N80D is a dual section 3-stage fully integrated Doherty MMIC solution using Ampleon's state of the art LDMOS technology. The carrier and peaking device, input splitter, output combiner and pre-match are integrated in each section. This multiband device is perfectly suited as general purpose driver in the frequency range 3300 MHz to 3800 MHz. Available in PQFN outline.

Table 1. Application performance

Typical RF performance at $T_{case} = 25$ °C; $I_{Dq} = 220$ mA (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65$ V. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB measured in an

 $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65$ V. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB measured in an Ampleon f = 3600 MHz integrated Doherty application circuit.

ľ	Test signal	f	V _{DS}	P _{L(AV)}	Gp	η _D
		(MHz)	(V)	(W)	(dB)	(%)
Ŀ	1-carrier LTE 20 MHz PAR = 7.6 dB	3600	28	5	33	21.5

1.2 Features and benefits

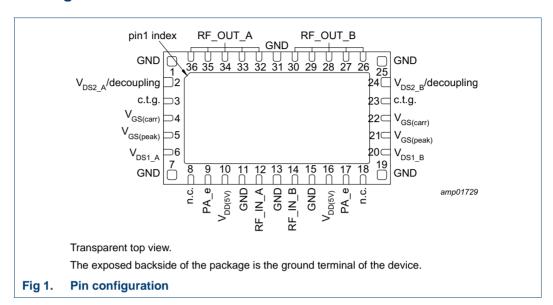
- Integrated input splitter
- Integrated output combiner
- lacksquare 25 Ω output impedance thanks to integrated pre-match
- Designed for wideband operation
- High linearity
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Integrated bias gate switch
- Source impedance 50 Ω ; high power gain
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

- Macrocell base station driver
- Microcell base station
- 5G mMIMO
- W-CDMA/LTE
- Active antenna
- General purpose applications

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
GND	1	ground
V _{DS2_A} /decoupling	2	drain-source voltage of final stages of section A
c.t.g.	3	connect to ground
V _{GS(carr)}	4	gate-source voltage of carrier [1]
V _{GS(peak)}	5	gate-source voltage of peaking [2]
V _{DS1_A}	6	drain-source voltage of driver stages of section A
GND	7	ground
n.c.	8	not connected
PA_e	9	PA enable trigger signal, 0 V to 5 V, I _{Dq} -bias ON/OFF corresponds to logic HIGH/LOW [3]
V _{DD(5V)}	10	supply voltage (5 V) [4]
GND	11	ground
RF_IN_A	12	RF input of section A
GND	13	ground
RF_IN_B	14	RF input of section B
GND	15	ground
V _{DD(5V)}	16	supply voltage (5 V) [4]
PA_e	17	PA enable trigger signal, 0 V to 5 V, I_{Dq} -bias ON/OFF corresponds to logic HIGH/LOW $\fbox{3}$
n.c.	18	not connected
GND	19	ground

Table 2. Pin description ...continued

Symbol	Pin	Description
V _{DS1_B}	20	drain-source voltage of driver stages of section B
V _{GS(peak)}	21	gate-source voltage of peaking [2]
V _{GS(carr)}	22	gate-source voltage of carrier [1]
c.t.g.	23	connect to ground
V _{DS2_B} /decoupling	24	drain-source voltage of final stages of section B
GND	25	ground
RF_OUT_B	26, 27, 28, 29, 30	RF output of section B
GND	31	ground
RF_OUT_A	32, 33, 34, 35, 36	RF output of section A

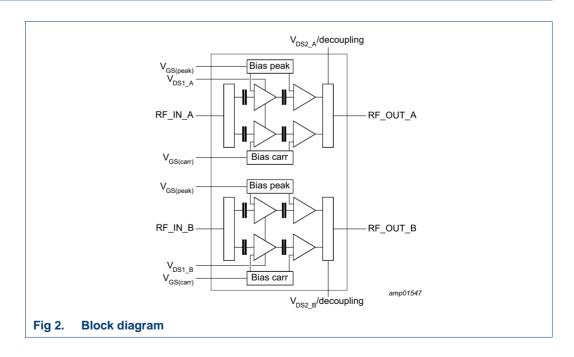
- [1] Pins connected together.
- [2] Pins connected together.
- [3] Pins connected together.
- [4] Pins connected together.

3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC	9 1111 1111	Min. orderable quantity (pieces)
PQFN-12x7-36-1	B11G3338N80DX	9349 604 70525	TR13; 1500-fold; 24 mm; dry pack	1500
PQFN-12x7-36-1	B11G3338N80DYZ	9349 604 70535	TR7; 300-fold; 24 mm; dry pack	300

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	200	°C

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

Symbol	Parameter	Conditions	Value	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 90 °C		
		P _L = 5 W [1]	1.7	K/W
		P _L = 10 W [1]	1.4	K/W

^[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

7. Characteristics

Table 6. DC characteristics

 $T_{case} = 25 \text{ °C}; V_{DD(5V)} = 5 \text{ V}; V_{on(PA_e)} = 5 \text{ V}.$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Carrier			<u> </u>			
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 210 \text{ mA}$	1.6	2.1	2.7	V
I _{GSS}	gate leakage current	V _{GS} = 2 V; V _{DS} = 0 V	-	-	140	nA
Peaking						
I _{GSS}	gate leakage current	$V_{GS} = 2 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
Final sta	ges					
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μΑ
Driver st	ages					
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	1.4	μΑ

Table 7. RF characteristics

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 210 mA (carrier); f = 3550 MHz; $V_{DD(5V)}$ = 4.8 V; $V_{on(PA_e)}$ = 5 V; $V_{GSq(peaking)}$ = $V_{GSq(carrier)}$ – 0.65 V; $P_{L(AV)}$ = 5 W; unless otherwise specified, measured in an Ampleon combined production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Test signal: pulsed CW [1]							
Gp	power gain	P _L = 5 W (37 dBm)	31	34	38	dB	
η_{D}	drain efficiency	P _L = 5 W (37 dBm)	18	25	-	%	
		$P_L = P_{L(3dB)}$	30	40	-	%	
RLin	input return loss		-	-15	-10	dB	
P _{L(3dB)}	output power at 3 dB gain compression		48	49	-	dBm	

^[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s).

8. Application information

8.1 Typical performance

Table 8. Typical performance

 $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 220$ mA (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65$ V; $V_{DD(5V)} = 5$ V; $V_{on(PA_e)} = 5$ V. Test signal: 1-carrier W-CDMA; PAR = 9.9 dB; unless otherwise specified, measured in an Ampleon 3300 MHz to 3800 MHz frequency band combined application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P _{L(1dB)}	output power at 1 dB gain compression	f = 3600 MHz	[1]	-	48.7	-	dBm
φ _{s21} /φ _{s21(norm)}	normalized phase response	at 1 dB compression point; f = 3600 MHz	[2]	-	-16	-	0
η _D	drain efficiency	12.2 dB OBO (P _{L(AV)} = 37 dBm); f = 3600 MHz		-	22	-	%
Gp	power gain	P _{L(AV)} = 37 dBm; f = 3600 MHz		-	33	-	dB
B _{video}	video bandwidth	P _{L(AV)} = 37 dBm set to obtain IMD3 = -45 dBc; f = 3600 MHz		-	350	-	MHz
G _{flat}	gain flatness	$P_{L(AV)} = 37 \text{ dBm}; f = 3300 \text{ MHz to}$ 3800 MHz		-	0.6	-	dB
ACPR _{20M}	adjacent channel power ratio (20 MHz)	P _{L(AV)} = 37 dBm; f = 3600 MHz		-	-39	-	dBc
ΔG/ΔΤ	gain variation with temperature	f = 3600 MHz		-	0.068	-	dB/°C
К	Rollett stability factor	$T_{case} = -40$ °C to +125 °C; f = 0.1 GHz to 8 GHz	[3]	-	>1	-	
Bias gate swit	tch						
t _r	rise time	Z_S = 500 Ω (max); T_{case} = -40 °C to +120 °C; $V_{on(PA_e)} \ge 4.8 \text{ V}$	[4]	-	200	-	ns
t _f	fall time	$T_{case} = -40 ^{\circ}\text{C} \text{ to } +120 ^{\circ}\text{C};$ $V_{off(PA_e)} \le 1 \text{V}$	[5]	-	80	-	ns

- [1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s).
- [2] 25 ms CW power sweep measurement.
- [3] With input VSWR better than 30:1 and output VSWR better than 80:1.
- [4] RF output rise time 10 % to 90 % RF power.
- [5] RF output fall time 90 % to 10 % RF power.

8.2 PCB layout and electrical schematic

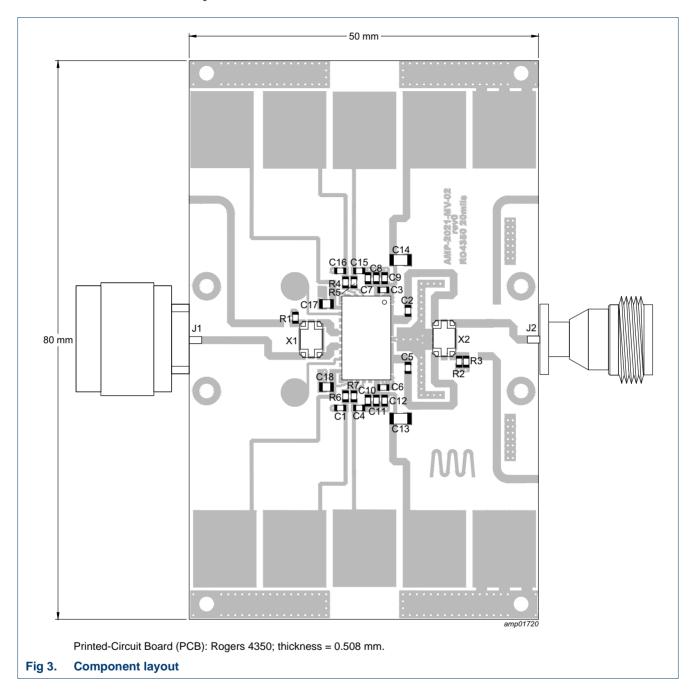


Table 9. Demo test circuit list of components

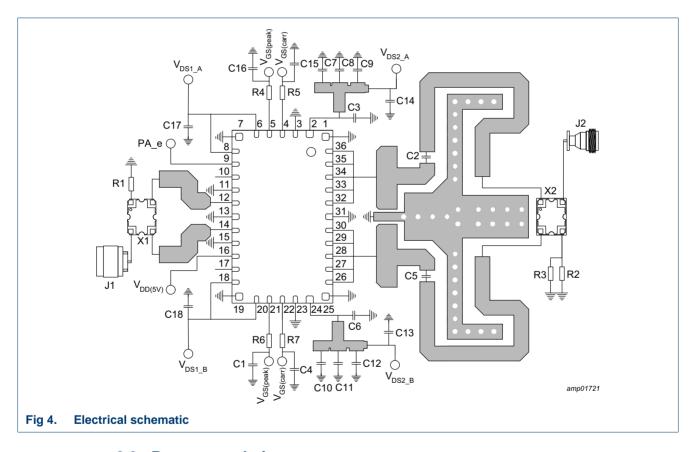
See Figure 3 for component layout.

Component	Description	Value	Remarks					
C1, C4, C15, C16	multilayer ceramic chip capacitor	1 μF, 50 V	Murata: C1608X5R1H105K080AB					
C2, C5	multilayer ceramic chip capacitor	1.6 pF, ± 0.1 %	Murata: GQM1875C2E1R6BB12					
C3, C6	multilayer ceramic chip capacitor	4.3 pF, ± 0.1 %	Murata: GQM1875C2E4R3BB12					

Table 9. Demo test circuit list of components ... continued

See Figure 3 for component layout.

Component	Description	Value	Remarks
C7, C8, C9, C10, C11, C12	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: 06035C104KAT2A
C13, C14, C17, C18	multilayer ceramic chip capacitor	10 μF, 50 V	Murata: GRM21BR6YA106KE43
R1	resistor	49.9 Ω , \pm 1 %, 100 mW	Multicomp Pro: MCWF06R49R9BTL
R2, R3	resistor	100 Ω , \pm 1 %, 200 mW	Multicomp Pro: MP001293
R4, R5, R6, R7	resistor	1 k Ω , \pm 1 %, 100 mW	Multicomp Pro: MCSR06X1001FTL
X1, X2	hybrid coupler	3.3 GHz – 3.8 GHz, 25 W	Anaren: X3C35F1-03S
J1	N Coaxial panel connector male		Radiall: R161.438.200
J2	N Coaxial panel connector female		Huber & Suhner: 23_N-50-0-16/133_NE



8.3 Recommendations

- RC circuit at gate bias must be implemented to insure improved linearity and stability of the circuit. The implementation has to be symmetrical between both amplifier sections Pin 5/21 and Pin 4/22.
- In TDD mode controlled by an external bias switch, the outputs of the switches must be connected on both amplifier sections. As shown in Fig.4, gate bias supply must be connected before RC circuit of Pin 5/21 and Pin 4/22 respectively by default.

8.4 Ruggedness in a Doherty operation

8.4.1 Output mismatch ruggedness

The B11G3338N80D is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 32 \text{ V}$; $I_{Dq} = 105 \text{ mA (carrier)}$; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65 \text{ V}$; $V_{DD(5V)} = 5 \text{ V}$; $V_{on(PA_e)} = 5 \text{ V}$; P_i corresponding to $P_{L(3dB)} - 9 \text{ dB}$ under $Z_S = 50 \Omega$ load; f = 3800 MHz (1-carrier W-CDMA); $T_{case} = 25 \,^{\circ}\text{C}$; per section.

8.4.2 Wideband noise ruggedness

The B11G3338N80D is capable of withstanding an AWGN (Additive White Gaussian Noise) with 11.2 dB PAR, OBW (Occupied BandWidth) of 900 MHz, under the following conditions: $V_{DS} = 32$ V; $I_{Dq} = 105$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65$ V; $V_{DD(5V)} = 5$ V; $V_{on(PA_e)} = 5$ V; 3 dB P_i overdrive from $P_{L(AV)} = 34$ dBm (corresponding to $P_{L(3dB)} - 12$ dB); f = 3550 MHz as central frequency; $T_{case} = 25$ °C; per section.

8.5 Impedance information

Table 10. Typical impedance for optimum Doherty operation

Measured load-pull data per section; test signal: pulsed CW; $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 105$ mA (carrier); $V_{DD(5V)} = 5$ V; $V_{on(PA_e)} = 5$ V; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65$ V; $t_p = 100$ μ s; $\delta = 10$ %.

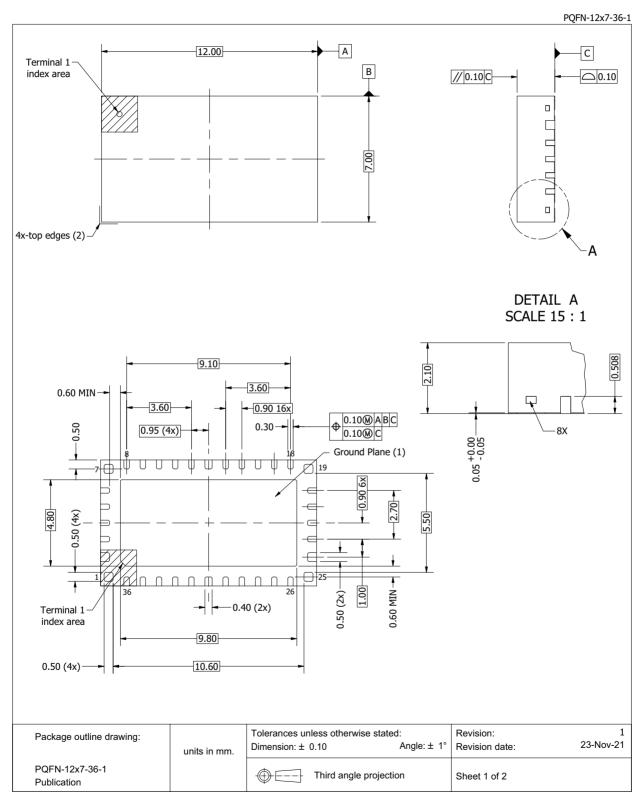
	tuned for optimu	tuned for optimum Doherty operation						
f	Z _L [1]	P _{L(1dB)}	G _{p(max)}	η _{add} [2]	η _{add} [3]			
(MHz)	(Ω)	(dBm)	(dB)	(%)	(%)			
3300	21.5 – j19.3	46.34	34.9	44.1	22.1			
3400	21.4 – j17.2	46.30	35.3	44.3	22.7			
3500	22.3 – j16.4	46.50	35.7	45.2	22.9			
3600	23.9 – j13.4	46.30	35.7	44.3	23.7			
3700	24.0 - j13.4	46.30	35.3	44.6	23.3			
3800	22.7 – j11.4	46.20	35.0	44.1	23.4			

^[1] Reference package plane.

^[2] At P_{L(1dB)}.

^[3] At 34 dBm.

Package outline 9.



Package outline PQFN-12x7-36-1 (sheet 1 of 2) Fig 5.

PQFN-12x7-36-1

Items (1) (2)	Terminals (bottom View), 0 Plastic protrusions of 0.07	Ground-plane (bot	Description tom View) and Lead step-cut are plated with materials.	te Sn	
(1)	Plastic protrusions of 0.07	Ground-plane (bot	tom View) and Lead step-cut are plated with mat	te Sn	
(2)	Plastic protrusions of 0.07				
		5 mm. max. per si	de are not included.		
Packa	age outline drawing:	units in mm.	Tolerances unless otherwise stated: Dimension: ± 0.10 Angle: ± 1°	Revision: Revision date:	23-Nov-

Fig 6. Package outline PQFN-12x7-36-1 (sheet 2 of 2)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C1 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C [2]

- [1] CDM classification C1 is granted to any part that passes after exposure to an ESD pulse of 250 V.
- [2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description
5G	Fifth Generation
CW	Continuous Wave
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
mMIMO	massive Multiple Input Multiple Output
MTF	Median Time to Failure
ОВО	Output Back Off
PA	Power Amplifier
PAR	Peak-to-Average power Ratio
RC	resistor-capacitor
RoHS	Restriction of Hazardous Substances
TDD	Time Division Duplex
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
B11G3338N80D v.2	20220407	Product data sheet	-	B11G3338N80D v.1
Modifications:	fications: • Table 3 on page 3: added second orderable part number			
	 Section 13.2 	on page 13: updated sec	tion	
	 Section 13.3 	3 on page 13: updated sec	tion	
B11G3338N80D v.1	20211217	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
2.1	Pinning
2.2	Pin description 2
3	Ordering information 3
4	Block diagram 3
5	Limiting values 4
6	Thermal characteristics 4
7	Characteristics 4
8	Application information 5
8.1	Typical performance 5
8.2	PCB layout and electrical schematic 6
8.3	Recommendations
8.4	Ruggedness in a Doherty operation 8
8.4.1	Output mismatch ruggedness
8.4.2	Wideband noise ruggedness 8
8.5	Impedance information 8
9	Package outline 9
10	Handling information 11
11	Abbreviations11
12	Revision history 12
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks14
14	Contact information 14
15	Contents 15

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